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(54) Title: TRANSISTOR WITH A PASSIVE GATE AND METHODS OF FABRICATING THE SAME

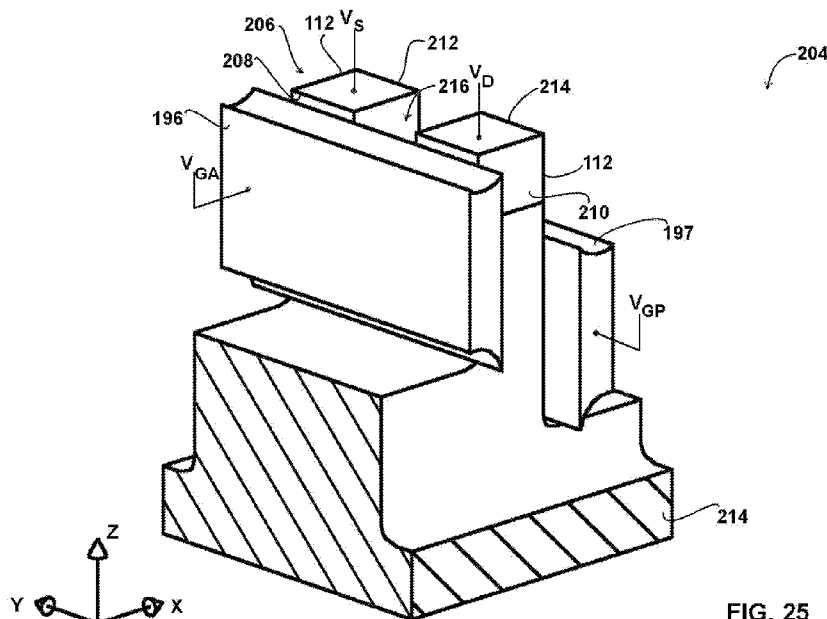


FIG. 25

(57) Abstract: Disclosed is a device having a transistor (204, 244, 286) that includes a source, a drain, a channel region extending between the source and the drain, a gate (196, 238, 284) disposed near the channel region, and a conductive member (197, 240, 264) disposed opposite of the channel region from the gate (196, 238, 284). The conductive member (197, 240, 264) may not overlap the source, the drain, or both the source and the drain.